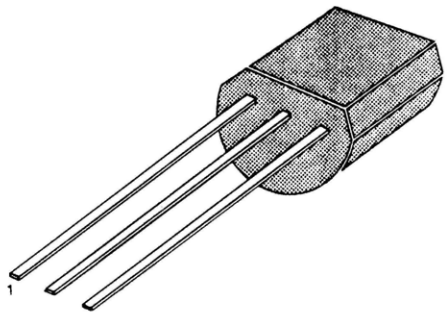
A1015
PNP Epitaxial Silicon Transistor

LOW FREQUENCY AMPLIFIER

- Collection Dissipation : P_C(max) = 400mW
- Collector-Emitter Voltage : V_{CEO} = -50V

TO - 92



1. Emitter 2. Collector 3. Base

Absolute Maximum Ratings (TA=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Collector Current	I_C	-150	mA
Collector Dissipation	P_C	400	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Characteristics (TA=25°C)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C= -100μA, I_E=0	-50		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C= -0.1mA, I_B=0	-50		V
Collector Cut-off Current	I_{CBO}	V_{CB}= -50V, I_E=0		-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}= -5V, I_C=0		-0.1	μA
DC Current Gain	h_{FE}	V_{CE}= -6V, I_C= -2mA	70	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C= -100mA, I_B= -10mA		-0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C= -100mA, I_B= -10mA		-1.1	V
Base-Emitter Voltage	V_{BE}	I_E= -310mA		-1.45	V
Transition Frequency	f_T	V_{CE}= -10V, I_C= -1mA			
		f=30MHz	80		MHz

h_{FE} CLASSIFICATION

Classification	O	Y	GR
h_{FE}	70-140	120-240	200-400

Elite Enterprises (H.K.) Co., Ltd.
Flat 2505, 25/F., Nanyang Plaza, 57 Hung To Road, Kwun Tong, H.K.
Tel: (852) 2723-3122 Fax: (852) 2723-3990 Email: info@elite-ent.com.hk